

产品规格书

Specifcation of products

产品名称:快恢复二极管

产品型号: MF500U6NK8

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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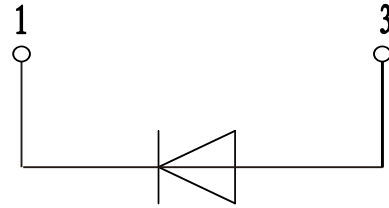
拟制	审核	核准
林益龙	曹剑龙	宗瑞

PRODUCT FEATURES

- ☑ Ultrafast Reverse Recovery Time
- ☑ Soft Reverse Recovery Characteristics
- ☑ Low Reverse Recovery Loss
- ☑ Low Forward Voltage
- ☑ High Surge Current Capability
- ☑ Low Inductance Package

APPLICATIONS

- ☑ Inversion Welder
- ☑ Uninterruptible Power Supply (UPS)
- ☑ Plating Power Supply
- ☑ Ultrasonic Cleaner and Welder
- ☑ Converter & Chopper
- ☑ Power Factor Correction (PFC) Circuit



ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
V_R	Maximum D.C. Reverse Voltage		600	V
V_{RRM}	Maximum Repetitive Reverse Voltage		600	V
$I_{F(AV)}$	Average Forward Current	$T_C=110^{\circ}\text{C}$, Per Moudle	500	A
$I_{F(RMS)}$	RMS Forward Current	$T_C=110^{\circ}\text{C}$, Per Diode	560	A
I_{FSM}	Non-Repetitive Surge Forward Current	$T_J=45^{\circ}\text{C}$, $t=10\text{ms}$, 50Hz, Sine	4500	A
		$T_J=45^{\circ}\text{C}$, $t=8.3\text{ms}$, 60Hz, Sine	4960	A
I^2t	I^2t (For Fusing)	$T_J=45^{\circ}\text{C}$, $t=10\text{ms}$, 50Hz, Sine	96000	A^2s
		$T_J=45^{\circ}\text{C}$, $t=8.3\text{ms}$, 60Hz, Sine	108375	A^2s
P_D	Power Dissipation		1050	W
T_J	Junction Temperature		-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range		-40 to +125	$^{\circ}\text{C}$
V_{isol}	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
Torque	Module-to-Sink	Recommended (M6)	3~5	N.M
Torque	Module Electrodes	Recommended (M6)	3~5	N.M
$R_{\theta JC}$	Thermal Resistance	Junction-to-Case	0.14	$^{\circ}\text{C} / \text{W}$
Weight			140	g

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{RM}	Reverse Leakage Current	V _R =600V	--	--	0.3	mA
		V _R =600V, T _J =125°C	--	--	10	mA
V _F	Forward Voltage	I _F =500A	--	1.45	--	V
		I _F =500A, T _J =125°C	--	1.25	--	V
t _{rr}	Reverse Recovery Time	I _F =1A, V _R =30V, di _F /dt=-200A/μs	--	180	--	ns
t _{rr}	Reverse Recovery Time	V _R =300V, I _F =500A	--	200	--	ns
I _{RRM}	Max. Reverse Recovery Current	di _F /dt=-200A/μs, T _J =25°C	--	12	--	A
t _{rr}	Reverse Recovery Time	V _R =300V, I _F =500A	--	260	--	ns
I _{RRM}	Max. Reverse Recovery Current	di _F /dt=-1000A/μs, T _J =125°C	--	20	--	A

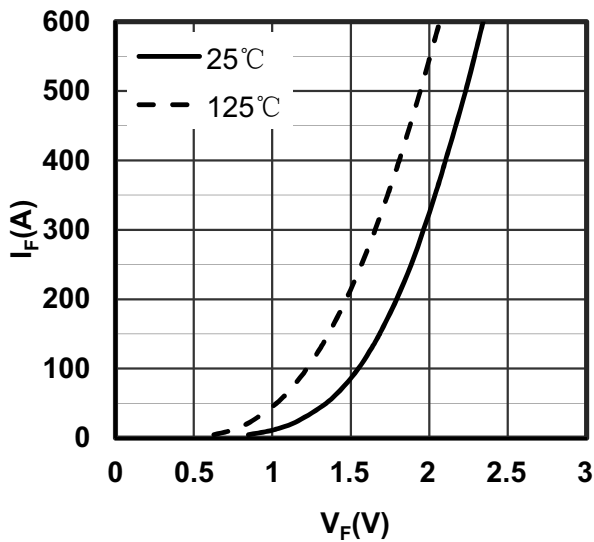


Figure1. Forward Voltage Drop vs Forward Current

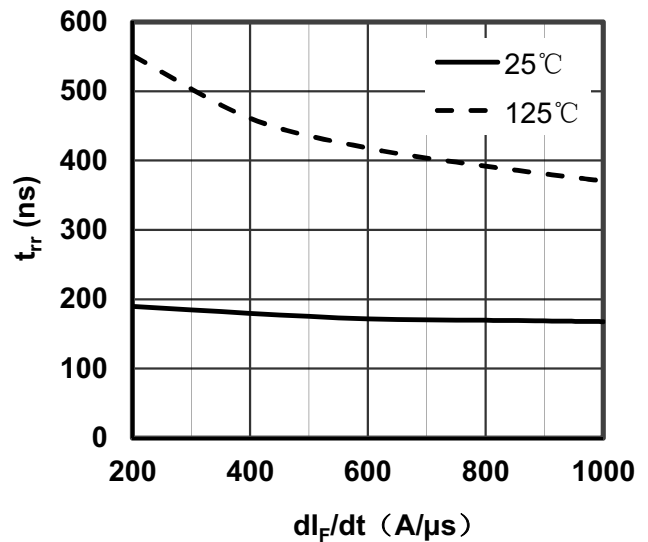


Figure2. Reverse Recovery Time vs di_F/dt

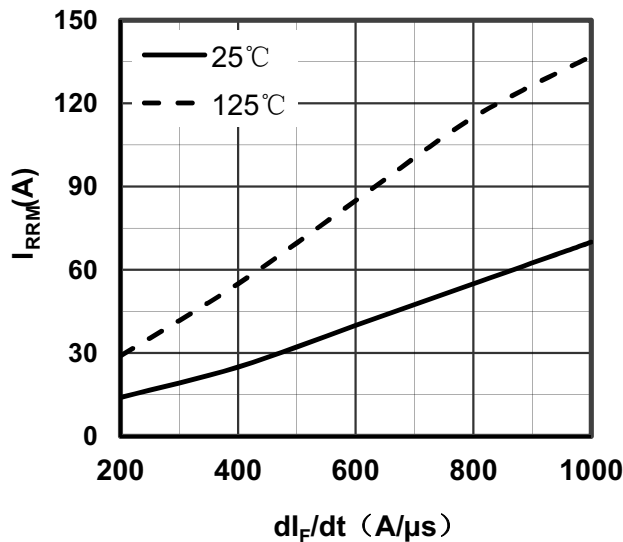


Figure3. Reverse Recovery Current vs di_F/dt

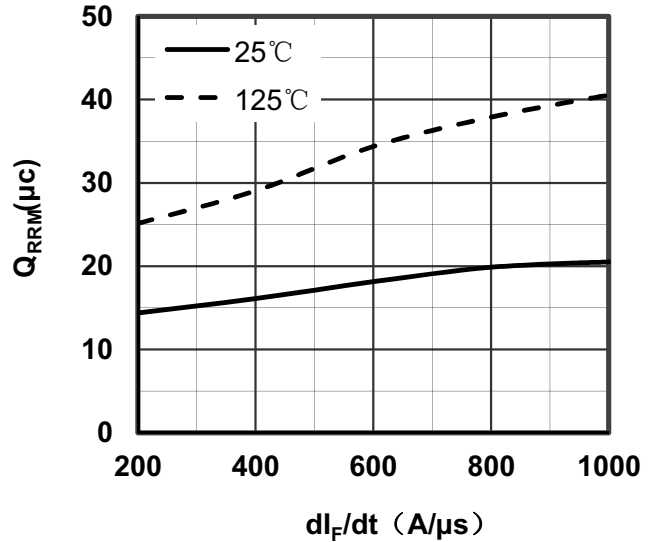


Figure4. Reverse Recovery Charge vs di_F/dt

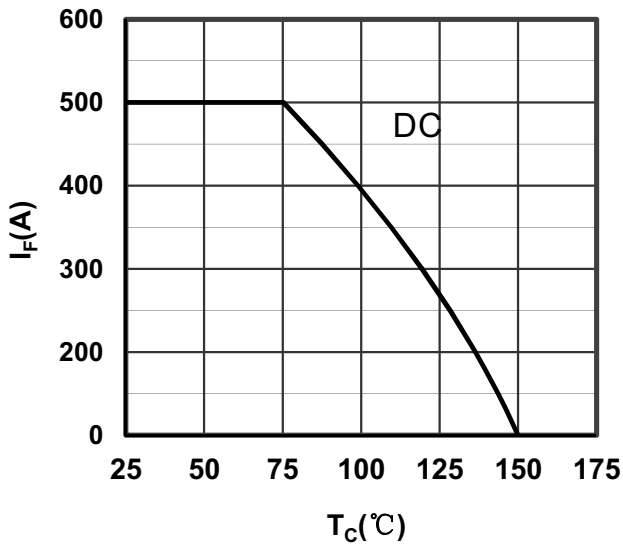


Figure 5. Forward current vs Case temperature

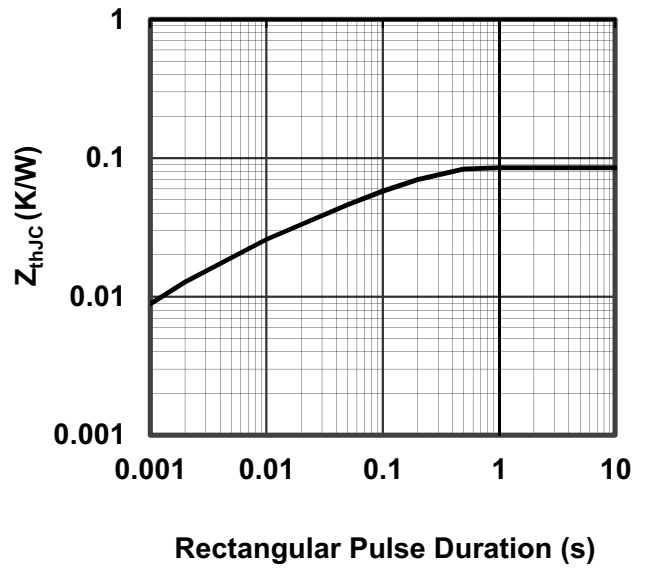
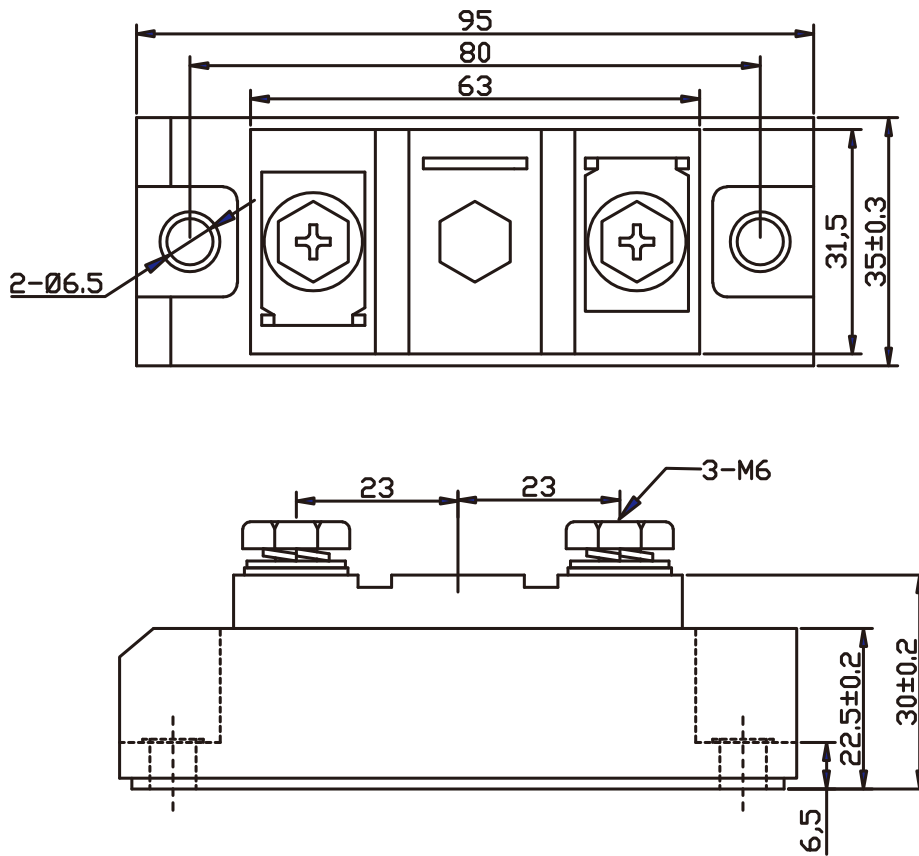


Figure 6. Transient Thermal Impedance



Unit:mm